

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

EPAS ID: PAT4024707

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
XIN LIN	08/22/2016
RONGHUA ZHU	08/22/2016
HONGNING YANG	08/20/2016
RECEIVING PARTY DATA	
Name:	Freescal Semiconductor, Inc.
Street Address:	6501 William Cannon Drive West
Internal Address:	Law Department
City:	Austin
State/Country:	TEXAS
Postal Code:	78735
PROPERTY NUMBERS Total: 1	
Property Type	Number
Application Number:	15242322
CORRESPONDENCE DATA	
Fax Number:	(512)895-6630
<i>Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.</i>	
Phone:	512-895-6979
Email:	sheena.hicks@nxp.com
Correspondent Name:	FREESCALE SEMICONDUCTOR, INC.
Address Line 1:	6501 WILLIAM CANNON DRIVE WEST
Address Line 2:	TX30/OE62
Address Line 4:	AUSTIN, TEXAS 78735
ATTORNEY DOCKET NUMBER:	81899865US01
NAME OF SUBMITTER:	SHEENA HICKS
SIGNATURE:	/Sheena Hicks/
DATE SIGNED:	08/25/2016
Total Attachments: 1	
source=81899865US01_Nonprovisional_Assignment#page1.tif	

Docket No. 81899865US01

ASSIGNMENT

For good and valuable consideration, receipt of which is hereby acknowledged, we, as below-named Assignor/s, hereby sell, assign, and transfer the entire and exclusive right, title, and interest in the following to **FREESCALE SEMICONDUCTOR, INC.**, having a place of business at 6501 William Cannon Drive, Austin, TX 78735, USA, its successors, assigns, and legal representatives, including any nominees (collectively "the Assignee"):

(1) our invention relating to "**LATERALLY DIFFUSED MOSFET WITH ISOLATION REGION**" for which the following patent application(s) has/have been filed (we hereby authorize and request my/our attorneys associated with U.S. Patent & Trademark Office Customer Number 65913 to insert below the filing date and application number of the U.S. application when known):

<u>Country</u>	<u>Application No.</u>	<u>Filing Date (mm/dd/yyyy)</u>	<u>Claims Priority of</u>
US	15/242,322	08/19/2016	

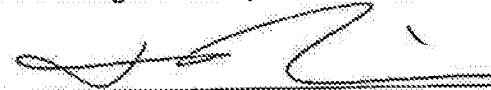
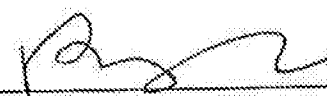
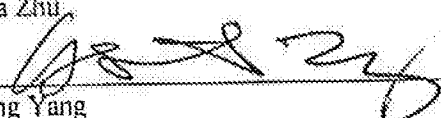
(2) the foregoing application(s) and all other United States, foreign and international patent applications associated therewith, based thereon, or claiming priority there from including, but not limited to, any and all provisionals, non-provisionals, divisions, continuations, continuations-in-part, re-examinations, reissues, and extensions thereof, and

(3) the right to claim priority thereto, and the entire and exclusive right, title, and interest in and to any and all patents granted on these applications.

We authorize and request that the Patent Office officials in the United States and in any and all foreign countries to issue any and all Letters Patent when granted, solely to **FREESCALE SEMICONDUCTOR, INC.**, for its sole use, and that of its successors, assigns, and legal representatives.

We will provide our cooperation to enable the Assignee to enjoy the foregoing right, title, and interest to the fullest extent. Upon request at the expense of the Assignee, we agree to execute all papers, take all rightful oaths, testify in all legal proceedings including patent prosecutorial actions and infringement actions, and do all other such acts which may be necessary, desirable, or convenient for securing and maintaining patents on the foregoing invention or for perfecting title thereto in the Assignee.

We certify that we have the full right to convey the above rights.

<u>8/22/2016</u> Date	 _____ Xin Lin	Assignor
<u>8/22/2016</u> Date	 _____ Ronghua Zhu	Assignor
<u>8/20/2016</u> Date	 _____ Hongning Yang	Assignor